L Number	Hits	Search Text	[·B	Tim⇔ stamp
11		"liner oxide"	USPAT; US-PGPUE	2001/05/31 12:38
14	1	("5,851,899").PN.	USPAT; US-PGPUP	20(1),(5,31 12:59
17	2.6 ri	"liner oxide" and trench	USPAT; US-EGEUB	1000, (5/31 13:10
26	7630	STI or "shallow trench" or "trench	USPAT; US-EGFUE	2000,05/01 13:10
2 9	958	isolation" (STI or "shallow trench" or "trench	USPAT;	::00.,(5 31 1::15)
69	461	isolation") and SOI ((STI or "shallow trench" or "trench isolation") and SOI) and (insulating ADJ2	USPAF; US-FGFUE	. (80) - 18 - 21 - 42121
7.5	371	layer) (((STI ir "shallow trench" or "trench isclation") and SII; and (insulating ADJ)	USPAT; US-EGEUE	.0002 05 01 13:35
78	303	<pre>layer)) and gate   (+ (STI or "shallow trench" or "trench   is.lation") and SEI+ and (insulating ADJ2   layer)) and gate: and (BPSG or TEGS or</pre>	USPAT; US-EGFUE	2007-05/71 13:35
91	- *1 	<pre>di-lectric) ( ST1 or "shallow trench" or "trench isolation") and SOT+ and ((insulating ADJ2-layer) SAME (BPSG or TEOS or dielectric))</pre>	USPAT; US-EGFUE	Sto. 35.11.131at
84	15:	((ESTI or "shallow trench" or "trench" isolation") and SOI: and ((insulating ADJ2 layer) SAME (BPSG or TEOS or dielectric)); and gate	USPAT; US-FGFUF	.002 05 31 13:45
87	4:	<pre>((((STI or "shallow trench" or "trench isolation") and SOI) and ((insulating ADJD layer) SAME (BPSG or TEOS or dielectric)); and gate) and FET</pre>	USPAT; US-EGEUB	200.705 01 13:45
90	5.3	((STI or "shallow trench" or "trench isolation") and SOI) and ((insulating ADJ2 layer) SAME (BESG or TEOS in dielectric) SAME (thickness or angstrom or ang))	USPAT; US-EGPUE	.00. 95 [1 14:00]
93	26	((:STI or "shallow trench" or "trench is:latith") and SOI) and ((insulating ADJ2 layer) SAME (BPSG or TEOS or dielectric) SAME (thickness :r angstrom or ang)) and FET	USPAT; USHEGEUE	E(0); 05 31 15:19
9€	1	("6363941").PN.	USPAT; US-FGEUF	20 to 05 51 15:19
-	1871))	"body contact" or "floating body" or "substrate contact"	USPAT; US-FGEUF	2000//05/29 11:31
-	441	(STI or "shallow trench" or "trench isolation") and ("body contact" or "floating body" or "substrate contact")	USPAT; US-EGEUB	2001 05 09 11:31
-	154	((STI or "shallow trench" or "trench isolation") and ("body contact" or "floating body" or "substrate contact")) and SOI	USPAT; US-FGPUB	2002105 29 15:52
-	946	(STI or "shallow trench" or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor or insulator")	USPAT; US-FGFUR	2001/05/29 16:32
-	738	((STI or "shallow trench" or "trench isplation": and (SOI or "silicon on insulator" or "semiconductor on	USPAT; US-ESPUB	20 (2 05/29 15:59
-	778	insulator")) and gate (('STI or "snallow trench" or "trench isolation", and .801 or "silicon on insulator" or "semiconductor or	USPAT; US-EGPUB	2 Ht. 105 129 16:23
-	490	insulator" ) and gate) and oxide (( (STI or "shallow trench" or "trench isolation") and (SDI or "silicon on insulator" or "semiconductor on insulator")) and gate) and oxide) and	USPAT; US-FGPUB	20u. 105 39 16:23
-	9075	<pre>("hard mask" or "silicon nitride") STI or ((shallow or deep) ADJ3 trenches) or "trench isolation"</pre>	USPAI; US-PGPUB	2002/05/29 16:31

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-	6424	SGI or "silicen on insulator" or "semiconductor on insulator"	USPAT; US-PGPUB	2002/.b-29 is:32
_	1103	(STI or ((shallow or deep: ADJ3 trenches)	USPAT;	2002/95/29 18:92
	1100	or "trench isolation") and (SOI or	US-PGPUB	
		"sillern on insulator" or "semicenductor		
		on insulator")		
-	1	("5504033").PN.	USPAT;	2002/05/29 16:39
			US-PGPUB	
	186	((STI or ((shallow or deep) AIJ3 trenches)	USPAT;	2002/05/30 12:22
		or "tren:h isclation") and (SCI or	US-PGPUE	
		"silicin on insulator" or "semiconductor		
		er. insulator":) and ("body contact" or		
		"floating body" or "substrate contact")	HOTAID.	2002/05/30 18:49
_	11116	((STI or ((shallow or deep) AEJ3 trenches)	USFAT; US-FGPUE	2002.00/20 20.49
		or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor	US-FISEUE	
		or insulator"))		
_	1084	(((STI or ((shallow or deep) ADJ3	USFAT;	2002,05,30 12:25
	1004	trenches) or "trench isolation") and (SOI	US-FGPUB	
		or "silicon on insulator" or		
		"semiconductor on insulator")) ) and oxide		
_	619	((((STI or ((shallow or deep) ADJ3	USFAT;	2002 05 30 18:39
		trenches; or "trench isolation") and (SCI	US-PGPUE	
		or "silicor or insulator" or		
		"semicenductor on insulator")) ) and		
		exide) and ("silicon nitride")		0162100 10 11.36
-		(("5,636,343") or ("5,631,776")).PN.	USFAT; US-FGPUF	2002 05 30 12:38
		"nebert of al." and "siliton nitride"	USFAT;	2002 Pf 35 12:38
	1.1	impert of al. and Siliton diffide	US-FGPUE	
_	1.20	((STI or ((shallow or deep) ADJ3	JSFAT;	2002 05 30 12:42
	4	trenches) or "trench isolation") and (SOI	US-PGPUE	
		or "silicen on insulator" or		
		"semiconductor on insulator")) ) and		
		oxide) and ("hard mask")		
-	·	"5683930").PN.	USFAT;	200. 05/30 12:43
		W6 11 6 4 0 1 10 4 10 11 7 0 4 7 0 11 11 17 11	US-PGPUP	2007/05/30 14:19
=		("5006482"   "5173439").PN.	USFAT USFAT	2002 05 30 14:22
-		5362541.UE.PN. PTI or "partial trench isolation"	USFAT;	200. 05 30 16:07
_	804	FIT of partial trench isolation.	US-PGPUB	2,0. 00 00 10.0
_	1 5	(PTI or "partial trench isolation"	USFAT;	2000105/30 18:39
_	1.0	) and SOI	US-PGPUE	
_	101	438/FDR.196.ccls.	EPO; JPO;	2002 05 30 15:47
	- / -		DEFWENT	
_	503	SOI and trench	EPO; JPO;	2002/05/30 18:47
			DEFWENT	
-	95		EPO; JPO;	2002/05/31 15:49
		or "trench isolation") and (SOI or	DEF.WENT	
		"silicon on insulator" or "semiconductor		
		on insulator"))		

L Number	Hits	Search Text	DB	Time stamp
1	0	sti with liner with soi	USPAT; US-PGPUB	2002/05/31 15:03
2	3586	sti	USPAT;	2002/05/31
3	59343	liner	US-PGPUB USPAT;	15:03 2002/05/31
			US-PGPUB	15:03
4	6435	soi	USPAT; US-PGPUB	2002/05/31 15:03
5	90	sti with liner	USPAT; US-PGPUB	2002/05/31 15:03
6	9	(sti with liner) and soi	USPAT;	2002/05/31
			US-PGPUB	15:04